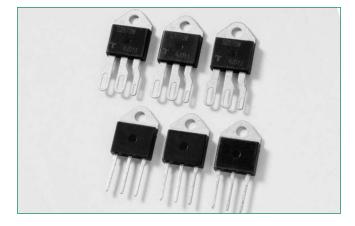
Qxx40xx Series



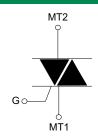
Agency Approval

Agency Agency File Number	
FU E71639*	

* - K and J Packages

Main Features					
Symbol	Value	Unit			
I _{T(RMS)}	40	A			
V _{DRM} /V _{RRM}	400 to 1000	V			
Ι _{GT (Ω1)}	35 to 100	mA			

Schematic Symbol



Description

The 40 Amp bi-directional solid state switch series is designed for AC switching and phase control applications such as motor speed, temperature modulation controls, lighting controls, and static switching relays.

Alternistor type components only operate in quadrants I, II, & III and are used in circuits requiring high dv/dt capability.

Standard type devices operate in quadrants I,II,III & IV.

Features & Benefits

- RoHS Compliant
- Glass passivated junctions

Voltage capability up to

 Surge capability up to 400A

RoHS

• Electrically isolated K & J -Packages are UL Recognized for 2500Vrms

Applications

1000V

Excellent for AC switching and phase control applications such as heating, lighting, and motor speed controls.

Typical applications are AC solid-state switches, industrial power tools, exercise equipment, white goods and commercial appliances.

Alternistor Triacs (no snubber required) are used in applications with extremely inductive loads requiring highest commutation performance.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.



Absolute Maximum Ratings – Alternistor Triac (3 Quadrants)

Symbol	Para	Value	Unit		
I _{T(RMS)}	RMS on-state current (full sine wave)	Qxx40x7 Qxx40xH6	T _c = 75 ℃	40	А
	Non repetitive surge peak on-state current	t = 20 ms	335	•	
TSM	(full cycle, TJ initial = 25°C)	f = 60 Hz	t = 16.7 ms	400	A
l²t	I2t Value for fusing	t _p = 8.3 ms	664	A²s	
di/dt	Critical rate of rise of on-state current (IG = $2 \times IGT$, tr $\leq 100 \text{ ns}$) f = 120 Hz		T _J = 125 °C	150	A/µs
I _{GTM}	Peak gate trigger current	t _p =20µs	T _J = 125 °C	4	А
P _{G(AV)}	Average gate power dissipation T _J = 125 °C				W
T _{stg}	Storage temperature range				°C
Tj	Operating junction temperature range				°C

Absolute Maximum Ratings – Standard Triac (4 Quadrants)

Symbol	Parameter	Test C	Test Conditions		Unit
I _{T(RMS)}	RMS on-state current	Qxx40x3/Qxx40x4	T _c = 75 °C	40	А
I	Deals non sonatitive auson aussent	f = 50 Hz	t = 20 ms	335	^
TSM	Peak non-repetitive surge current	f = 60 Hz	t = 16 ms	400	A
l²t	I²t Value for fusing		t _p = 8.3 ms	664	A²s
di/dt	Critical rate-of-rise of on-state current	f = 120 Hz; T _J =125 °C		150	A/µs
I _{gtm}	Peak gate current	t _p =20µs	T _J = 125 °C	4	А
P _{G(AV)}	Average gate power dissipation	T_ =	= 125°C	0.5	W
T _{stg}	Storage temperature range			-40 to 150	°C
T,	Operating junction temperature range			-40 to 125	°C

Electrical Characteristics (T₁ = 25°C, unless otherwise specified) – Alternistor Triac (3 Quadrants)

Symbol	Test Conditions	Quadrant			Value		Unit
Зушьог				Qxx40xH6	Qxx40K5	Qxx40x7	Unit
I _{gt}	$V_{D} = 12V R_{L} = 60 \Omega$	1 – 11 – 111	MAX.	80	50	100	mA
V _{gt}	$V_{_D} = 12V R_{_L} = 60 \Omega$	1 – 11 – 111	MAX.	1.3	1.3	2.0	V
V _{gd}	$V_{\rm D} = V_{\rm DRM}$ $R_{\rm L} = 3.3$ k Ω $T_{\rm J} = 125^{\circ}{\rm C}$	1 – 11 – 111	MIN.	0.2		V	
I _H	I _T = 400mA		MAX.	80	75	100	mA
		400V		600	500	700	
-1 (-1.4	$V_{D} = V_{DRM}$ Gate Open $T_{J} = 125^{\circ}C$	600V		500	475	625	\//
dv/dt		800V	MIN.	475	400	575	V/µs
	$V_{\rm D} = V_{\rm DRM}$ Gate Open $T_{\rm J} = 100^{\circ}{\rm C}$	1000V				500	
(dv/dt)c	(di/dt)c = 21.6 A/ms T _J = 125°C		MIN.	30	20	50	V/µs
t _{gt}	$I_{g} = 2 \times I_{gT} PW = 15 \mu s I_{T} = 56.$	6A(pk)	TYP.		5		μs

Electrical Characteristics ($T_1 = 25^{\circ}C$, unless otherwise specified) — Standard Triac (4 Quadrants)

Symbol	Test Conditions	Qua	drant	Qxx40x3	Value Qxx40x4	Unit
		- -	MAX.	35	50	
GT	$V_{_{D}} = 12 \text{ V}; \text{ R}_{_{L}} = 60 \Omega$	IV	MAX.	70	100	- mA
V _{gt}	$V_{_{D}} = 12 \text{ V}; \text{ R}_{_{L}} = 60 \Omega$	ALL	MAX.	1.3	1.3	V
V _{gd}	$V_{_{ m D}} = V_{_{ m DRM}}$; $R_{_{ m L}} = 3.3 \text{ k}\Omega$; $T_{_{ m J}} = 125 \text{ °C}$	ALL	MIN.	0.2	0.2	V
I _H	$I_{\tau} = 400 \text{mA} \text{ (initial)}$		MAX.	80	80	mA
		400V		400	400	
dv/dt	$V_{D} = V_{DRM}$; Gate Open; $T_{J} = 125 \text{ °C}$	600V	MIN.	400	400	V/µs
	800V		-	400	400	
(dv/dt)c	(di/dt)c = 4.3 A/ms; T _J = 125 °C		MIN.	10	10	V/µs
t _{gt}	I _G = 2 × I _{GT} ; PW = 15μs; I _T = 35.4 A		TYP.	5	5	μs
dv/dt	VD=VDRM,Gate Open, TJ=100°C 100	00V	-	-	300	V/µs

Static Characteristics

Symbol	Test Conditions					Unit
V _{TM}	$I_{TM} = 56.6A t_p = 380 \ \mu s$	$T_J = 25^{\circ}C$	MAX.		1.8	V
		$T_J = 25^{\circ}C$	400-1000V	MAX.	20	μA
l _{DRM}	$V_{\rm d} = V_{\rm drm} / V_{\rm rrm}$	$T_J = 125^{\circ}C$	400 - 800V	MAX.	5	mA
RRM		$T_J = 100^{\circ}C$	1000V	MAX.	5	mA

Thermal Resistances

Symbol	Parameter		Value	Unit	
R _{e(J-C)}	Junction to case (AC)		Qxx40KH6 Qxx40K5/7 Qxx40K4/J4 Qxx40K3	0.97	°C/W
			Qxx40JH6 Qxx40J7	0.95	

Note: xx = voltage



4.0

3.0

2.0

1.0

0.0

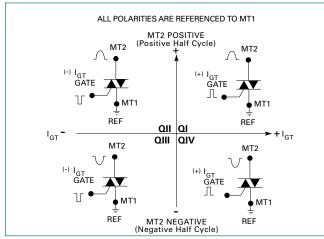
-40

-15

10

Ratio of $I_{\rm GT}$ / $I_{\rm GT}$ (T_J = 25°C)

Figure 1: Definition of Quadrants



Note: Alternistors will not operate in QIV

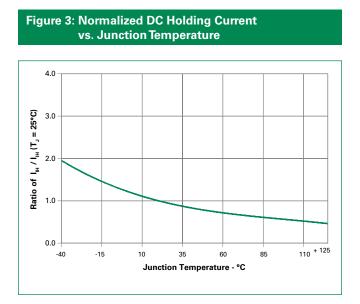


Figure 4: Normalized DC Gate Trigger Voltage for All Quadrants vs. Junction Temperature



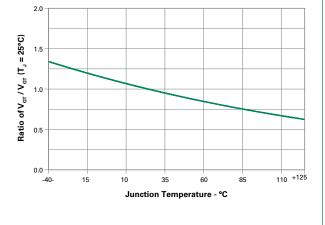
35

Junction Temperature -- (°C)

60

85

110 +125



All Quadrants vs. Junction Temperature

Figure 2: Normalized DC Gate Trigger Current for



Thyristors 40 Amp Alternistor (High Commutation) and Standard Triacs

Figure 5: Power Dissipation (Typical)

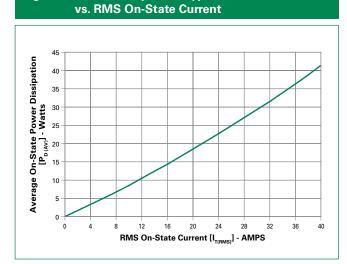


Figure 7: On-State Current vs. On-State Voltage (Typical)

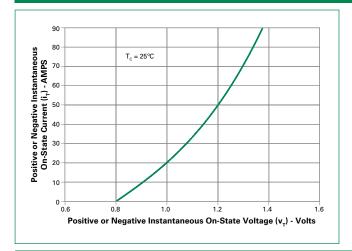
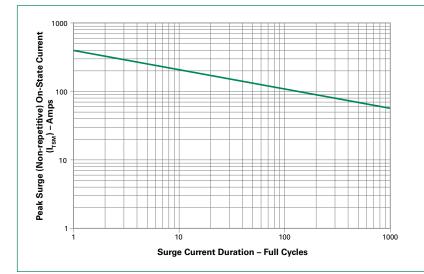
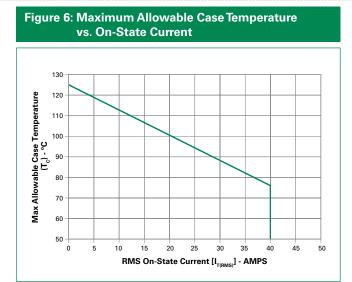


Figure 8: Surge Peak On-State Current vs. Number of Cycles





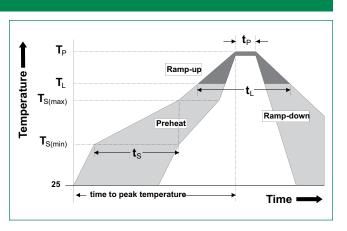
Supply Frequency: 60Hz Sinusoidal Load: Resistive RMS On-State [I_{T(RMS)}]: Max Rated Value at Specific Case Temperature

Notes:

- a) Gate control may be lost during and immediately following surge current interval.
 b) Overload may not be repeated until junction temperature has returned to steady-state
- rated value.

Soldering Parameters

Reflow Con	dition	Pb – Free assembly	
	- Temperature Min (T _{s(min)})	150°C	
Pre Heat	- Temperature Max (T _{s(max)})	200°C	
	- Time (min to max) (t _s)	60 – 180 secs	
Average ran peak	np up rate (Liquidus Temp) (T _L) to	5°C/second max	
T _{S(max)} to T _L - Ramp-up Rate		5°C/second max	
Reflow	- Temperature (T _L) (Liquidus)	217°C	
nellow	- Time (min to max) (t _s)	60 – 150 seconds	
Peak Tempe	rature (T _p)	260 ^{+0/-5} °C	
Time within (t _p)	s 5°C of actual peak Temperature	20 – 40 seconds	
Ramp-down Rate		5°C/second max	
Time 25°C t	o peak Temperature (T _p)	8 minutes Max.	
Do not exce	ed	280°C	



Environmental Specifications

AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

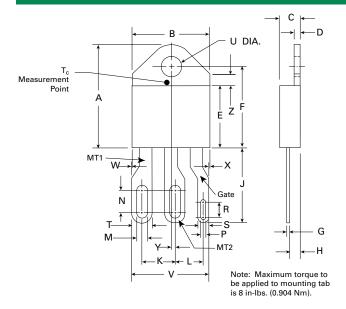
Physical Specifications				
Terminal Finish	100% Matte Tin-plated.			
Body Material	UL Recognized compound meeting flammability rating V-0			
Lead Material	Copper Alloy			

Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

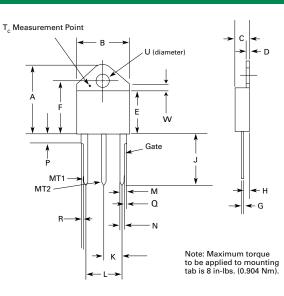


Dimensions – TO-218X (J Package) – Isolated Mounting Tab



Dimension	Inc	hes	Millin	neters
Dimension	Min	Max	Min	Max
А	0.810	0.835	20.57	21.21
В	0.610	0.630	15.49	16.00
С	0.178	0.188	4.52	4.78
D	0.055	0.070	1.40	1.78
E	0.487	0.497	12.37	12.62
F	0.635	0.655	16.13	16.64
G	0.022	0.029	0.56	0.74
Н	0.075	0.095	1.91	2.41
J	0.575	0.625	14.61	15.88
К	0.256	0.264	6.50	6.71
L	0.220	0.228	5.58	5.79
М	0.080	0.088	2.03	2.24
Ν	0.169	0.177	4.29	4.49
Р	0.034	0.042	0.86	1.07
R	0.113	0.121	2.87	3.07
S	0.086	0.096	2.18	2.44
Т	0.156	0.166	3.96	4.22
U	0.161	0.165	4.10	4.20
V	0.603	0.618	15.31	15.70
W	0.000	0.005	0.00	0.13
Х	0.003	0.012	0.07	0.30
Y	0.028	0.032	0.71	0.81
Z	0.085	0.095	2.17	2.42

Dimensions – TO-218AC (K Package) – Isolated Mounting Tab



Dimension	Inc	hes	Millimeters		
Dimension	Min	Мах	Min	Мах	
А	0.810	0.835	20.57	21.21	
В	0.610	0.630	15.49	16.00	
С	0.178	0.188	4.52	4.78	
D	0.055	0.070	1.40	1.78	
Е	0.487	0.497	12.37	12.62	
F	0.635	0.655	16.13	16.64	
G	0.022	0.029	0.56	0.74	
Н	0.075	0.095	1.91	2.41	
J	0.575	0.625	14.61	15.88	
К	0.211	0.219	5.36	5.56	
L	0.422	0.437	10.72	11.10	
Μ	0.058	0.068	1.47	1.73	
Ν	0.045	0.055	1.14	1.40	
Р	0.095	0.115	2.41	2.92	
Q	0.008	0.016	0.20	0.41	
R	0.008	0.016	0.20	0.41	
U	0.161	0.165	4.10	4.20	
W	0.085	0.095	2.17	2.42	

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Product Selector

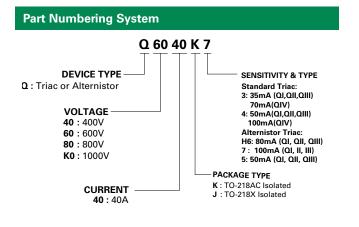
	Voltage		Gate Sensitivity Quadrants			_			
Part Number	400V	600V	800V	1000V	1 - 11 - 111	IV	T(RMS)	Туре	Package
Qxx40KH6	Х	Х	Х	Х	80 mA	-	40 A	Alternistor Triac	TO-218AC
Qxx40JH6	Х	Х	Х	-	80 mA	-	40 A	Alternistor Triac	TO-218X
Qxx40K5	Х	Х	Х	-	50 mA	-	40 A	Alternistor Triac	TO-218AC
Qxx40K7	Х	Х	Х	Х	100 mA	-	40 A	Alternistor Triac	TO-218AC
Qxx40J7	Х	Х	Х	-	100 mA	-	40 A	Alternistor Triac	TO-218X
Qxx40K4	Х	Х	Х	Х	50 mA	100 mA	40 A	Standard Triac	TO-218AC
Qxx40K3	-	-	Х	-	35 mA	70 mA	40 A	Standard Triac	TO-218AC
Qxx40J4	-	-	-	Х	50mA	100mA	40 A	Standard Triac	TO-218X

Note: xx = Voltage

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx40KH6TP	Qxx40KH6	4.40 g	Tube Pack	250 (25 per tube)
Qxx40JH6TP	Qxx40JH6	5.23 g	Tube Pack	250 (25 per tube)
Qxx40K5TP	Qxx40K5	4.40 g	Tube Pack	250 (25 per tube)
Qxx40K7TP	Qxx40K7	4.40 g	Tube Pack	250 (25 per tube)
Qxx40J7TP	Qxx40J7	5.23 g	Tube Pack	250 (25 per tube)
Qxx40K4TP	Qxx40K4	4.40 g	Tube Pack	250 (25 per tube)
Qxx40K3TP	Qxx40K3	4.40g	Tube Pack	250(25 per tube)
Qxx40J4TP	Qxx40J4	5.23g	Tube Pack	250(25 per tube)

Note: xx = Voltage



Part Marking System

TO-218 AC - (K Package) TO-218 X - (J Package) 06040K7

